

# Fully Integrated, Hall Effect-Based Linear Current Sensor with 3 kVRMS Voltage Isolation and a Low-Resistance Current Conductor

#### **Features and Benefits**

- Industry-leading noise performance through proprietary amplifier and filter design techniques
- Total output error 0.8% at  $T_A = 25$ °C
- Small package size, with easy mounting capability
- Monolithic Hall IC for high reliability
- Ultra-low power loss: 130  $\mu\Omega$  internal conductor resistance
- 3 kV<sub>RMS</sub> minimum isolation voltage from pins 1-3 to pins 4-5
- 3.0 to 5.0 V, single supply operation
- 3 μs output rise time in response to step input current
- 20 or 40 mV/A output sensitivity
- Output voltage proportional to AC or DC currents
- Factory-trimmed for accuracy
- Extremely stable output offset voltage
- Nearly zero magnetic hysteresis

### Package: 5 pin module (suffix PFF)



Additional leadforms available for qualifying volumes

#### Description

The Allegro ACS756 family of current sensors provides economical and precise solutions for AC or DC current sensing in industrial, automotive, commercial, and communications systems. The device package allows for easy implementation by the customer. Typical applications include motor control, load detection and management, power supplies, and overcurrent fault protection.

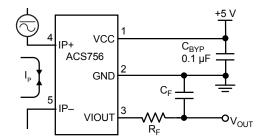
The device consists of a precision, low-offset linear Hall sensor circuit with a copper conduction path located near the die. Applied current flowing through this copper conduction path generates a magnetic field which is sensed by the integrated Hall IC and converted into a proportional voltage. Device accuracy is optimized through the close proximity of the magnetic signal to the Hall transducer. A precise, proportional voltage is provided by the low-offset, chopper-stabilized BiCMOS Hall IC, which is programmed for accuracy at the factory.

The output of the device has a positive slope ( $>V_{\rm CC}/2$ ) when an increasing current flows through the primary copper conduction path (from terminal 4 to terminal 5), which is the path used for current sensing. The internal resistance of this conductive path is 130  $\mu\Omega$  typical, providing low power loss.

Continued on the next page...

Engineering samples available on a limited basis. Contact your local sales or applications support office for additional information.

## **Typical Application**



Application 1. The ACS756 outputs an analog signal,  $V_{OUT}$ , that varies linearly with the uni- or bi-directional AC or DC primary sensed current,  $I_P$ , within the range specified.  $C_F$  is for optimal noise management, with values that depend on the application.

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#### **Description (continued)**

The thickness of the copper conductor allows survival of the device at up to 5× overcurrent conditions. The terminals of the conductive path are electrically isolated from the sensor leads (pins 1 through 3). This allows the ACS756 family of sensors to be used in applications requiring electrical isolation without the use of opto-isolators or other costly isolation techniques.

The device is fully calibrated prior to shipment from the factory. The ACS75x family is lead (Pb) free. All leads are plated with 100% matte tin, and there is no Pb inside the package. The heavy gauge leadframe is made of oxygen-free copper.

#### **Selection Guide**

Part Number <sup>1</sup>	T <sub>OP</sub> (°C)	Primary Sensed Current , I <sub>P</sub> (A)	Packing <sup>2</sup>
ACS756SCA-050B-PFF-T	-20 to 85	±50	
ACS756SCA-100B-PFF-T	–20 to 85	±100	34 per tube
ACS756KCA-050B-PFF-T	-40 to 125	±50	



#### **Absolute Maximum Ratings**

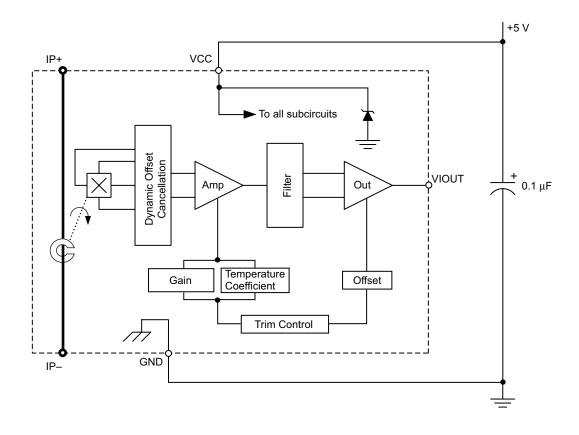
Characteristic	Symbol	Notes	Rating	Units
Forward Supply Voltage	V <sub>CC</sub>		8	V
Reverse Supply Voltage	V <sub>RCC</sub>		-0.5	V
Rated Input Voltage	V <sub>WORKING</sub>	Voltage applied to leadframe (IP+ pins)	353	VAC
Forward Output Voltage	V <sub>IOUT</sub>		28	V
Reverse Output Voltage	V <sub>RIOUT</sub>		-0.5	V
Reinforced Isolation Voltage	V <sub>ISO</sub>	Pins 1-3 and 4-5; 60 Hz, 1 minute; T <sub>A</sub> = 25°C	3000	V
Output Source Current	I <sub>OUT(Source)</sub>	VIOUT to GND	3	mA
Output Sink Current	I <sub>OUT(Sink)</sub>	VCC to VIOUT	1	mA
Naminal Operating Ambient Temperature	_	Range K	-40 to 125	°C
Nominal Operating Ambient Temperature	T <sub>OP</sub>	Range S	–20 to 85	°C
Maximum Junction	T <sub>J</sub> (max)		165	°C
Storage Temperature	T <sub>stg</sub>		-65 to 165	°C



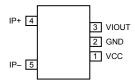
<sup>&</sup>lt;sup>1</sup>Additional leadform options available for qualified volumes

<sup>&</sup>lt;sup>2</sup>Contact Allegro for additional packing options.

### **Functional Block Diagram**



### **Pin-out Diagram**



#### **Terminal List Table**

Number	Name	Description
1	VCC	Device power supply terminal
2	GND	Signal ground terminal
3	VIOUT	Analog output signal
4	IP+	Terminal for current being sensed
5	IP-	Terminal for current being sensed



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# Fully Integrated, Hall Effect-Based Linear Current Sensor with 3 kVRMS Voltage Isolation and a Low-Resistance Current Conductor

### COMMON OPERATING CHARACTERISTICS<sup>1</sup> over full range of T<sub>OP</sub>, and V<sub>CC</sub> = 5 V, unless otherwise specified

Characteristic	Symbol	Test Conditions	Min.	Тур.	Max.	Units
Supply Voltage	V <sub>cc</sub>		3	5.0	5.5	V
Supply Current	I <sub>CC</sub>	V <sub>CC</sub> = 5.0 V, output open	_	10	14	mA
Power On Time	t <sub>PO</sub>	T <sub>A</sub> = 25°C	_	35	_	μs
Rise Time	t <sub>r</sub>	$I_P$ = three-quarter scale of $I_P$ +, $T_A$ = 25°C, $C_{OUT}$ = 0.47 nF	_	3	_	μs
Internal Bandwidth <sup>2</sup>	BW <sub>i</sub>	-3 dB; I <sub>P</sub> is 10 A peak-to-peak; 100 pF from VIOUT to GND	-	120	-	kHz
Output Load Resistance	R <sub>LOAD(MIN)</sub>	VIOUT to GND	4.7	_	-	kΩ
Output Load Capacitance	C <sub>LOAD(MAX)</sub>	VIOUT to GND	-	_	10	nF
Primary Conductor Resistance	R <sub>PRIMARY</sub>	T <sub>A</sub> = 25°C	_	130	-	μΩ
Symmetry	E <sub>SYM</sub>	Over half-scale of lp	98.5	100	101.5	%
Bidirectional 0 A Output	V <sub>OUT(QBI)</sub>	I <sub>P</sub> = 0 A, T <sub>A</sub> = 25°C	_	V <sub>CC</sub> /2	_	V
Magnetic Offset Error	I <sub>ERROM</sub>	I <sub>P</sub> = 0 A, after excursion of 100 A	_	±0.23	_	Α
Ratiometry	V <sub>RAT</sub>	V <sub>CC</sub> = 4.5 to 5.5 V	_	100	_	%
Propagation Time	t <sub>PROP</sub>	T <sub>A</sub> = 25°C, C <sub>OUT</sub> = 100 pF,	_	1	_	μs

<sup>&</sup>lt;sup>1</sup>Device is factory-trimmed at 5 V, for optimal accuracy.



<sup>&</sup>lt;sup>2</sup>Guaranteed by design.

## Fully Integrated, Hall Effect-Based Linear Current Sensor with 3 kVRMS Voltage Isolation and a Low-Resistance Current Conductor

## X050 PERFORMANCE CHARACTERISTICS over Range K1: T<sub>OP</sub> = -40°C to 125°C, V<sub>CC</sub> = 5 V, unless otherwise specified

Characteristic	Symbol	Test Conditions	Min.	Тур.	Max.	Units
Primary Sensed Current	I <sub>P</sub>		-50	_	50	Α
Sensitivity	Sens <sub>TA</sub>	Half scale of I <sub>P</sub> applied for 5 ms, T <sub>A</sub> = 25°C	_	40	-	mV/A
Sensitivity	Sens <sub>TOP</sub>	Half scale of I <sub>P</sub> applied for 5 ms	37.2	_	42.8	mV/A
Noise <sup>2</sup>	V <sub>NOISE</sub>	T <sub>A</sub> = 25°C, 10 nF on VIOUT pin to GND	_	10	-	mV
Nonlinearity	E <sub>LIN(HT)</sub>	Up to full scale of I <sub>P</sub> , I <sub>P</sub> applied for 5 ms, T <sub>OP</sub> = 25°C to 125°C	<b>–</b> 1	_	1	%
	E <sub>LIN(LT)</sub>	Up to full scale of $I_P$ , $I_P$ applied for 5 ms, $T_{OP} = -40^{\circ}$ C to 25°C	- 1.8	_	1.8	%
	V <sub>OE(TA)</sub>	$I_P = 0 \text{ A}, T_A = 25^{\circ}\text{C}$	_	±2	-	mV
Electrical Offset Voltage <sup>3</sup>	V <sub>OE(TOP)HT</sub>	I <sub>P</sub> = 0 A, T <sub>OP</sub> = 25°C to 125°C	-30	_	30	mV
	V <sub>OE(TOP)LT</sub>	$I_P = 0 \text{ A}, T_{OP} = -40^{\circ}\text{C} \text{ to } 25^{\circ}\text{C}$	-60	_	60	mV
Total Output Error <sup>4</sup>	E <sub>TOT(HT)</sub>	Over full scale of I <sub>P</sub> , I <sub>P</sub> applied for 5 ms, T <sub>OP</sub> = 25°C to 125°C	-7.5	_	7.5	%
	E <sub>TOT(LT)</sub>	Over full scale of I <sub>P</sub> , I <sub>P</sub> applied for 5 ms, T <sub>OP</sub> = -40°C to 25°C	-7.5	_	7.5	%

Device may be operated at higher primary current levels, I<sub>P</sub>, and ambient temperatures, T<sub>OP</sub>, provided that the Maximum Junction Temperature,

### X050 PERFORMANCE CHARACTERISTICS over Range S1: T<sub>OP</sub> = -20°C to 85°C, V<sub>CC</sub> = 5 V, unless otherwise specified

Characteristic	Symbol	Test Conditions	Min.	Тур.	Max.	Units
Primary Sensed Current	Ι <sub>P</sub>		-50	-	50	Α
Sensitivity	Sens <sub>TA</sub>	Half scale of I <sub>P</sub> applied for 5 ms, T <sub>A</sub> = 25°C	_	40	_	mV/A
Gensitivity	Sens <sub>TOP</sub>	Half scale of I <sub>P</sub> applied for 5 ms	38.3	_	41.7	mV/A
Noise <sup>2</sup>	V <sub>NOISE</sub>	T <sub>A</sub> = 25°C, 10 nF on VIOUT pin to GND	_	10	-	mV
Nonlinearity	E <sub>LIN(HT)</sub>	Up to full scale of I <sub>P</sub> , I <sub>P</sub> applied for 5 ms, T <sub>OP</sub> = 25°C to 85°C	<b>–</b> 1	_	1	%
	E <sub>LIN(LT)</sub>	Up to full scale of $I_P$ , $I_P$ applied for 5 ms, $T_{OP} = -20^{\circ}\text{C}$ to 25°C	<b>–</b> 1	_	1	%
	V <sub>OE(TA)</sub>	I <sub>P</sub> = 0 A, T <sub>A</sub> = 25°C	_	±2	-	mV
Electrical Offset Voltage <sup>3</sup>	V <sub>OE(TOP)HT</sub>	I <sub>P</sub> = 0 A, T <sub>OP</sub> = 25°C to 85°C	-30	_	30	mV
	V <sub>OE(TOP)LT</sub>	$I_P = 0 \text{ A}, T_{OP} = -20^{\circ}\text{C to } 25^{\circ}\text{C}$	-30	_	30	mV
Total Output Error <sup>4</sup>	E <sub>TOT(HT)</sub>	Over full scale of I <sub>P</sub> , I <sub>P</sub> applied for 5 ms, T <sub>OP</sub> = 25°C to 85°C	<b>-</b> 5	_	5	%
	E <sub>TOT(LT)</sub>	Over full scale of $I_P$ , $I_P$ applied for 5 ms, $T_{OP}$ = $-20$ °C to 25°C	<b>-</b> 5	_	5	%

<sup>&</sup>lt;sup>1</sup>Device may be operated at higher primary current levels, I<sub>P</sub>, and ambient temperatures, T<sub>OP</sub>, provided that the Maximum Junction Temperature,  $T_J(max)$ , is not exceeded.



 $T_J(max)$ , is not exceeded.

<sup>&</sup>lt;sup>2</sup>6σ noise voltage.

 $<sup>^3</sup>$ V<sub>OE(TOP)</sub> drift is referred to ideal V<sub>OE</sub> = 2.5 V at 0 A.  $^4$ Percentage of I<sub>P</sub>, with I<sub>P</sub> = 25 A. Output filtered.

<sup>&</sup>lt;sup>2</sup>6σ noise voltage.

 $<sup>^3</sup>$ V<sub>OE(TOP)</sub> drift is referred to ideal V<sub>OE</sub> = 2.5 V at 0 A.  $^4$ Percentage of I<sub>P</sub>, with I<sub>P</sub> = 25 A. Output filtered.

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## X100 PERFORMANCE CHARACTERISTICS over Range S1: T<sub>OP</sub> = -20°C to 85°C, V<sub>CC</sub> = 5 V, unless otherwise specified

Characteristic	Symbol	Test Conditions	Min.	Тур.	Max.	Units
Primary Sensed Current	I <sub>P</sub>		-100	_	100	Α
Sensitivity	Sens <sub>TA</sub>	Half scale of I <sub>P</sub> applied for 5 ms, T <sub>A</sub> = 25°C	_	20	-	mV/A
Sensitivity	Sens <sub>TOP</sub>	Half scale of I <sub>P</sub> applied for 5 ms	18.2	_	21.8	mV/A
Noise <sup>2</sup>	V <sub>NOISE</sub>	T <sub>A</sub> = 25°C, 10 nF on VIOUT pin to GND	_	6	-	mV
Nonlinearity	E <sub>LIN(HT)</sub>	Up to full scale of I <sub>P</sub> , I <sub>P</sub> applied for 5 ms, T <sub>OP</sub> = 25°C to 85°C	- 1.75	_	1.75	%
	E <sub>LIN(LT)</sub>	Up to full scale of $I_P$ , $I_P$ applied for 5 ms, $T_{OP} = -20^{\circ}\text{C}$ to 25°C	<b>–</b> 1	_	1	%
	V <sub>OE(TA)</sub>	$I_P = 0 \text{ A}, T_A = 25^{\circ}\text{C}$	_	±2	-	mV
Electrical Offset Voltage <sup>3</sup>	V <sub>OE(TOP)HT</sub>	I <sub>P</sub> = 0 A, T <sub>OP</sub> = 25°C to 85°C	-30	_	30	mV
	V <sub>OE(TOP)LT</sub>	$I_P = 0 \text{ A}, T_{OP} = -20^{\circ}\text{C to } 25^{\circ}\text{C}$	-30	_	30	mV
Total Output Error <sup>4</sup>	E <sub>TOT(HT)</sub>	Over full scale of I <sub>P</sub> , I <sub>P</sub> applied for 5 ms, T <sub>OP</sub> = 25°C to 85°C	-8	_	8	%
	E <sub>TOT(LT)</sub>	Over full scale of I <sub>P</sub> , I <sub>P</sub> applied for 5 ms, T <sub>OP</sub> = -20°C to 25°C	-7	_	7	%

<sup>&</sup>lt;sup>1</sup>Device may be operated at higher primary current levels, I<sub>P</sub>, and ambient temperatures, T<sub>OP</sub>, provided that the Maximum Junction Temperature,



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T<sub>.I</sub>(max), is not exceeded.

<sup>&</sup>lt;sup>2</sup>6σ noise voltage.

 $<sup>^{3}</sup>V_{OE(TOP)}$  drift is referred to ideal  $V_{OE}$  = 2.5 V at 0 A.  $^{4}Percentage$  of  $I_{P}$ , with  $I_{P}$  = 25 A. Output filtered.

## **Definitions of Accuracy Characteristics**

**Sensitivity (Sens).** The change in sensor output in response to a 1 A change through the primary conductor. The sensitivity is the product of the magnetic circuit sensitivity (G/A) and the linear IC amplifier gain (mV/G). The linear IC amplifier gain is programmed at the factory to optimize the sensitivity (mV/A) for the half-scale current of the device.

**Noise** ( $V_{NOISE}$ ). The noise floor is derived from the thermal and shot noise observed in Hall elements. Dividing the noise (mV) by the sensitivity (mV/A) provides the smallest current that the device is able to resolve.

Nonlinearity ( $E_{LIN}$ ). The degree to which the voltage output from the sensor varies in direct proportion to the primary current through its half-scale amplitude. Nonlinearity in the output can be attributed to the saturation of the flux concentrator approaching the half-scale current. The following equation is used to derive the linearity:

$$100 \left\{ 1 - \left[ \frac{\Delta \text{ gain} \times \% \text{ sat ( } V_{\text{IOUT\_half-scale amperes } - V_{\text{IOUT(Q)}})}}{2 \left( V_{\text{IOUT\_quarter-scale amperes } - V_{\text{IOUT(Q)}} \right)} \right] \right\}$$

where

 $\Delta$  gain = the gain variation as a function of temperature changes from 25°C,

% sat = the percentage of saturation of the flux concentrator, which becomes significant as the current being sensed approaches half-scale  $\pm I_P$ , and

 $V_{IOUT\_half\text{-scale amperes}} = \text{the output voltage (V) when the sensed current approximates half-scale} \pm I_P \,.$ 

**Symmetry (E\_{SYM}).** The degree to which the absolute voltage output from the sensor varies in proportion to either a positive or negative half-scale primary current. The following equation is used to derive symmetry:

$$100 \left( \frac{V_{\text{IOUT}} + \text{half-scale amperes}^{-V_{\text{IOUT}}(Q)}}{V_{\text{IOUT}(Q)} - V_{\text{IOUT}} - \text{half-scale amperes}} \right)$$

**Ratiometry.** The device features a ratiometric output. This means that the quiescent voltage output,  $V_{IOUTQ}$ , and the magnetic sensitivity, Sens, are proportional to the supply voltage,  $V_{CC}$ .

The ratiometric change (%) in the quiescent voltage output is defined as:

$$\Delta V_{\text{IOUTQ}(\Delta V)} = \frac{V_{\text{IOUTQ}(V_{\text{CC}})} / V_{\text{IOUTQ}(5V)}}{V_{\text{CC}} / 5 \text{ V}} \times 100\%$$

and the ratiometric change (%) in sensitivity is defined as:

$$\Delta Sens_{(\Delta V)} = \frac{Sens_{(V_{CC})} / Sens_{(5V)}}{V_{CC} / 5 V} \times 100\%$$

**Quiescent output voltage (V**<sub>IOUT(Q)</sub>). The output of the sensor when the primary current is zero. For a unipolar supply voltage, it nominally remains at V<sub>CC</sub>/2. Thus, V<sub>CC</sub> = 5 V translates into V<sub>IOUT(Q)</sub> = 2.5 V. Variation in V<sub>OUT(Q)</sub> can be attributed to the resolution of the Allegro linear IC quiescent voltage trim, magnetic hysteresis, and thermal drift.

Electrical offset voltage ( $V_{OE}$ ). The deviation of the device output from its ideal quiescent value of  $V_{CC}/2$  due to nonmagnetic causes.

**Magnetic offset error (I** $_{\rm ERROM}$ ). The magnetic offset is due to the residual magnetism (remnant field) of the core material. The magnetic offset error is highest when the magnetic circuit has been saturated, usually when the device has been subjected to a full-scale or high-current overload condition. The magnetic offset is largely dependent on the material used as a flux concentrator. The larger magnetic offsets are observed at the lower operating temperatures.

**Total Output Error (E\_{TOT}).** The maximum deviation of the actual output from its ideal value, also referred to as *accuracy*, illustrated graphically in the output voltage versus current chart on the following page.

 $E_{TOT}$  is divided into four areas:

- **0 A at 25°C.** Accuracy of sensing zero current flow at 25°C, without the effects of temperature.
- **0** A over Δ temperature. Accuracy of sensing zero current flow including temperature effects.
- Half-scale current at 25°C. Accuracy of sensing the half-scale current at 25°C, without the effects of temperature.
- Half-scale current over Δ temperature. Accuracy of sensing half-scale current flow including temperature effects.

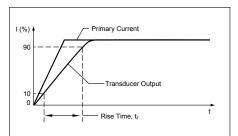


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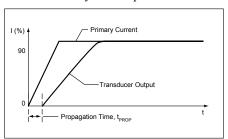
## **Definitions of Dynamic Response Characteristics**

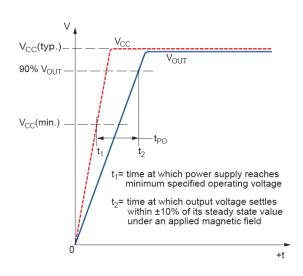
**Power-On Time (t<sub>PO</sub>).** When the supply is ramped to its operating voltage, the device requires a finite time to power its internal components before responding to an input magnetic field. Power-On Time,  $t_{PO}$ , is defined as the time it takes for the output voltage to settle within  $\pm 10\%$  of its steady state value under an applied magnetic field, after the power supply has reached its minimum specified operating voltage,  $V_{CC}(min)$ , as shown in the chart at right.

**Rise time** ( $t_r$ ). The time interval between a) when the sensor reaches 10% of its full scale value, and b) when it reaches 90% of its full scale value. The rise time to a step response is used to derive the bandwidth of the current sensor, in which  $f(-3 \text{ dB}) = 0.35/t_r$ . Both  $t_r$  and  $t_{RESPONSE}$  are detrimentally affected by eddy current losses observed in the conductive IC ground plane.



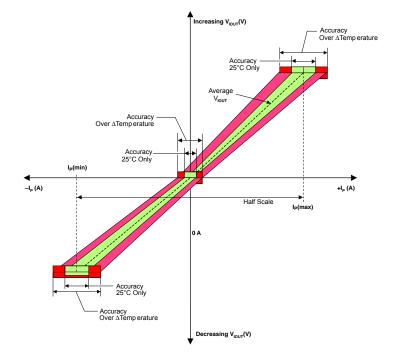
**Propagation delay (t<sub>PROP</sub>).** The time required for the sensor output to reflect a change in the primary current signal. Propagation delay is attributed to inductive loading within the linear IC package, as well as in the inductive loop formed by the primary conductor geometry. Propagation delay can be considered as a fixed time offset and may be compensated.





# Output Voltage versus Sensed Current Total Output Error at 0 A and at Half-Scale Current

Total Output Error at 0 A and at Half-Scale Current



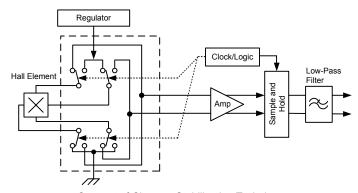


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#### **Chopper Stabilization Technique**

Chopper Stabilization is an innovative circuit technique that is used to minimize the offset voltage of a Hall element and an associated on-chip amplifier. Allegro patented a Chopper Stabilization technique that nearly eliminates Hall IC output drift induced by temperature or package stress effects. This offset reduction technique is based on a signal modulation-demodulation process. Modulation is used to separate the undesired DC offset signal from the magnetically induced signal in the frequency domain. Then, using a low-pass filter, the modulated DC offset is suppressed while the magnetically induced signal passes through the filter. As a result of this chopper stabilization approach, the output voltage from the Hall IC is desensitized to the effects of temperature and mechanical stress. This technique produces devices that have an extremely stable Electrical Offset Voltage, are immune to thermal stress, and have precise recoverability after temperature cycling.

This technique is made possible through the use of a BiCMOS process that allows the use of low-offset and low-noise amplifiers in combination with high-density logic integration and sample and hold circuits.



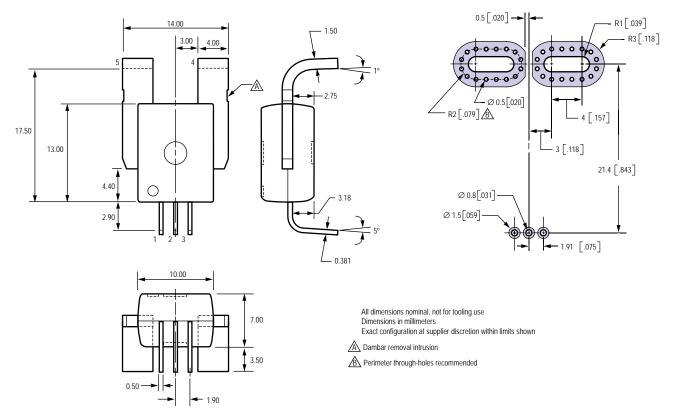
Concept of Chopper Stabilization Technique



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# Fully Integrated, Hall Effect-Based Linear Current Sensor with 3 kVRMS Voltage Isolation and a Low-Resistance Current Conductor

## Package CA, 5-pin module, leadform PFF



Creepage distance, current terminals to sensor pins: 7.25 mm Clearance distance, current terminals to sensor pins: 7.25 mm Package mass: 4.63 g typical

### **Package Branding**

Two alternative patterns are used

	ACS	Allegro Current Sensor
	756	Device family number
ACS756	R	Operating ambient temperature range code
RCAPPP	CA	Package type designator
	PPP	Primary sensed current
YYWWA	YY	Date code: Calendar year (last two digits)
	WW	Date code: Calendar week
	Α	Date code: Shift code

	ACS	Allegro Current Sensor
	756	Device family number
ACS756	R	Operating ambient temperature range code
<i>R</i> CA <i>PPP</i>	CA	Package type designator
LL	PPP	Primary sensed current
YYWW	LL	Lot code
	YY	Date code: Calendar year (last two digits)
	WW	Date code: Calendar week

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